FKP0139

FETek Technology Corp.

P-Ch 100V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

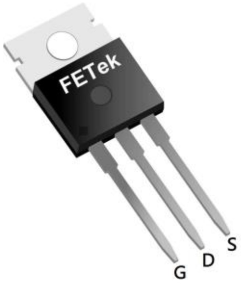
BVDSS	RDSON	ID
-100V	50mΩ	-35A

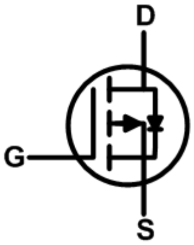
Description

The FKP0139 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The FKP0139 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO220 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ -10V[1]	-35	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ -10V[1]	-23	A
I_{DM}	Pulsed Drain Current[2]	-100	A
EAS	Single Pulse Avalanche Energy[3]	345	mJ
I_{AS}	Avalanche Current	28	A
P_D@T_C=25°C	Total Power Dissipation[4]	104	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.2	°C/W

Electrical Characteristics (T_J=25 ˚C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-10A	---	42	50	mΩ
		V_{GS}=-4.5V , I_D=-8A	---	46	55	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.8	-2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V , T_J=25˚C	---	---	-50	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-10A	---	32	---	S
Q_g	Total Gate Charge	V_{DS}=-80V , V_{GS}=-10V , I_D=-14A	---	92	---	nC
Q_{gs}	Gate-Source Charge		---	17.5	---	
Q_{gd}	Gate-Drain Charge		---	14	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-50V , V_{GS}=-10V , R_G=3.3Ω, I_D=-14A	---	20.5	---	ns
T_r	Rise Time		---	32.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	123	---	
T_f	Fall Time		---	63.7	---	
C_{iss}	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , f=1MHz	---	6516	---	pF
C_{oss}	Output Capacitance		---	223	---	
C_{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-35	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25˚C	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=-14A , di/dt=-100A/µs , T_J=25˚C	---	31.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	31.97	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.88mH,I_{AS}=-28A
4.The power dissipation is limited by 150˚C junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

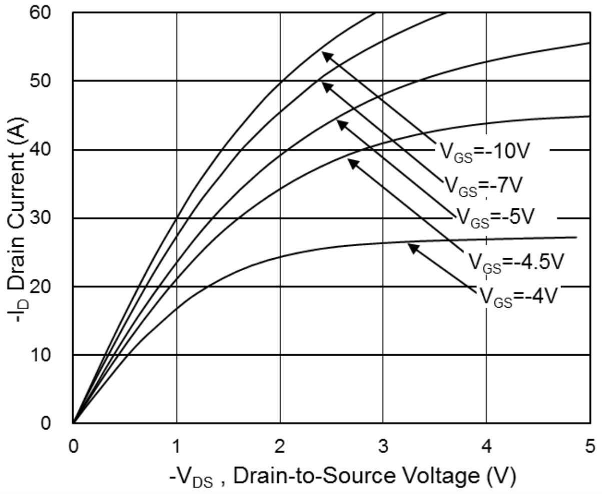


Fig.1 Typical Output Characteristics

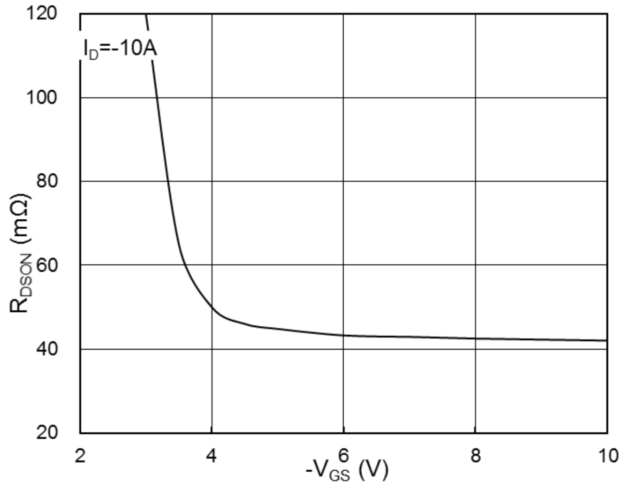


Fig.2 On-Resistance vs. G-S Voltage

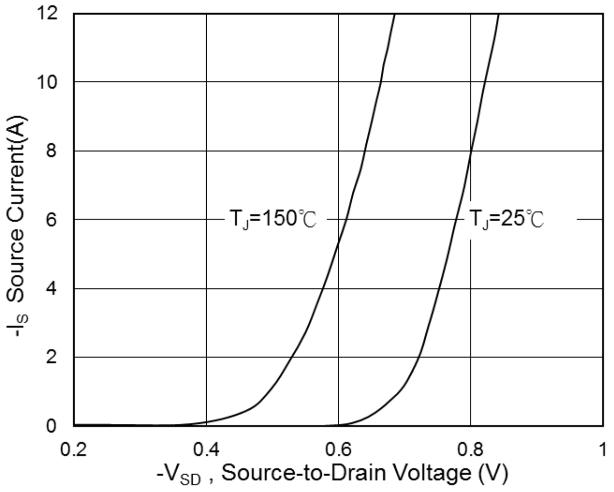


Fig.3 Typical S-D Diode Forward Voltage

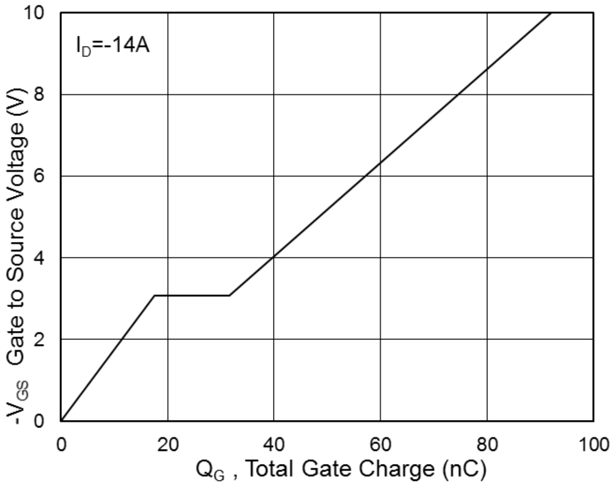


Fig.4 Gate-Charge Characteristics

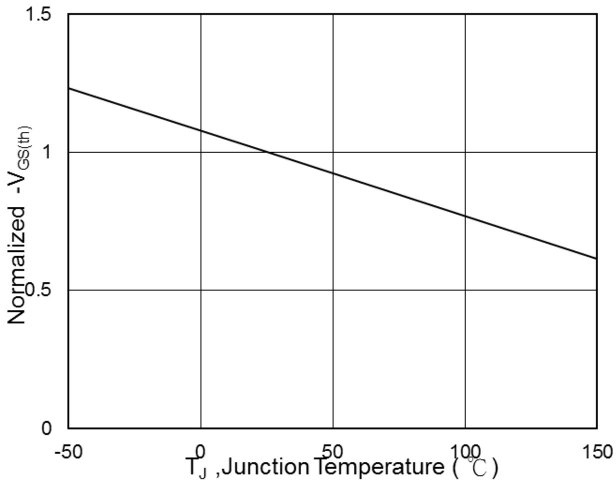


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

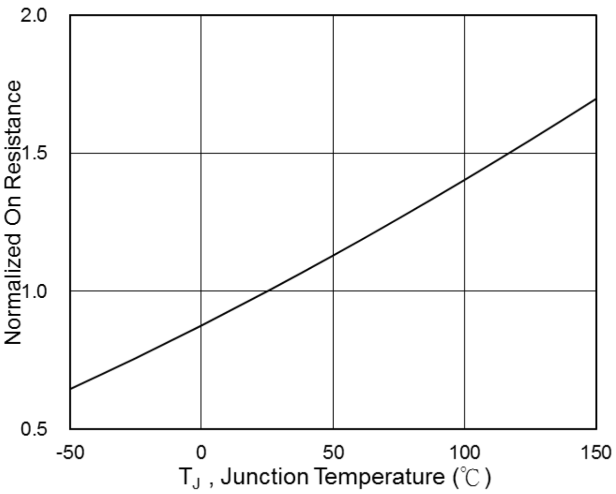


Fig.6 Normalized R_{DSON} vs. T_J

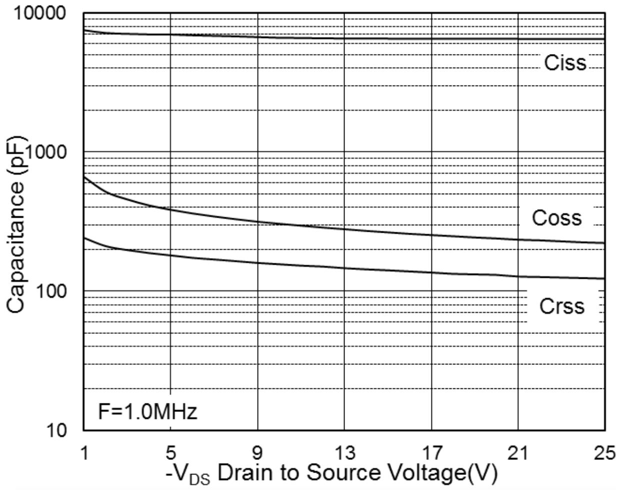


Fig.7 Capacitance

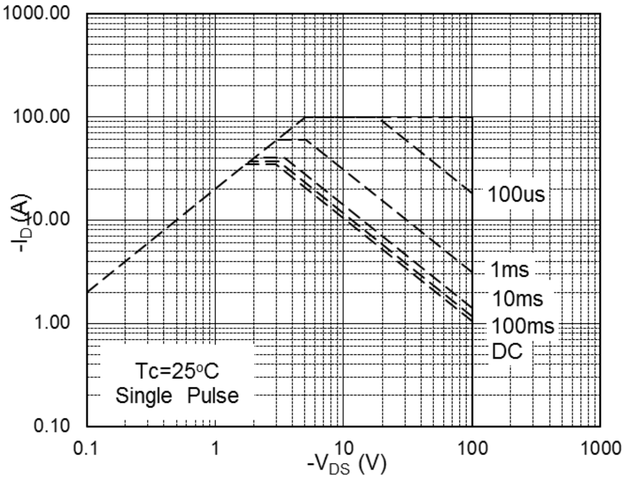


Fig.8 Safe Operating Area

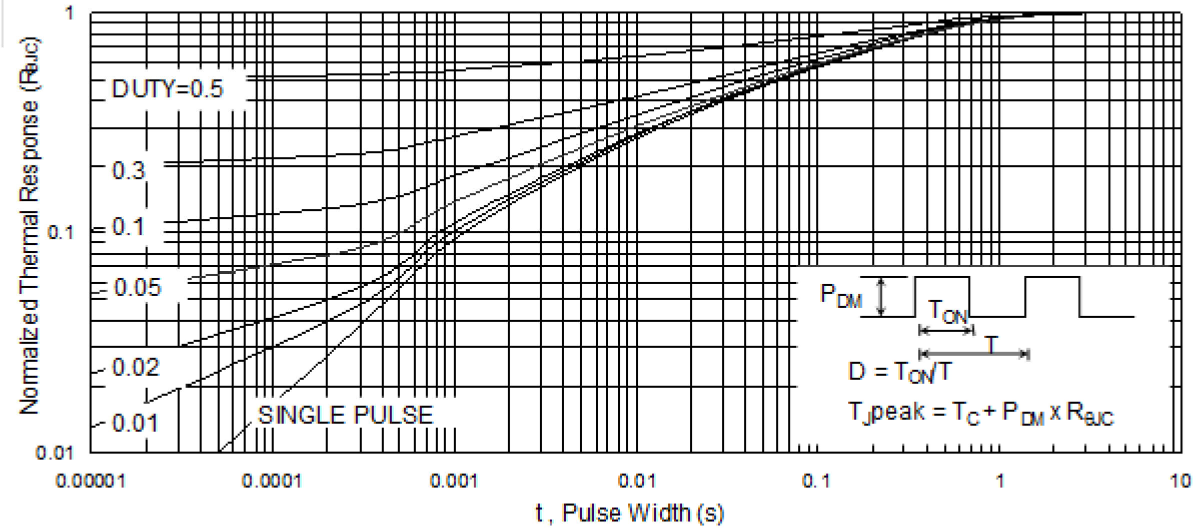


Fig.9 Normalized Maximum Transient Thermal Impedance

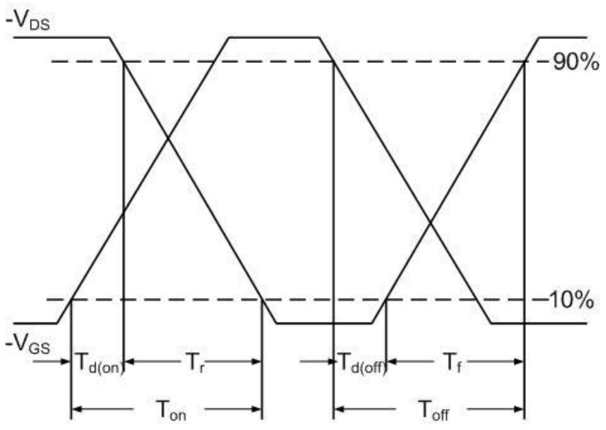


Fig.10 Switching Time Waveform

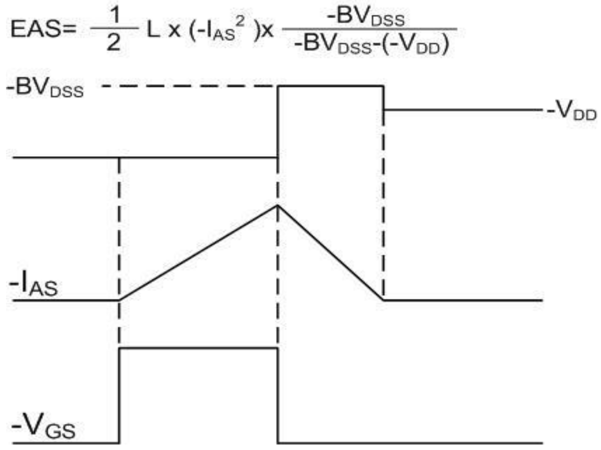


Fig.11 Unclamped Inductive Waveform